

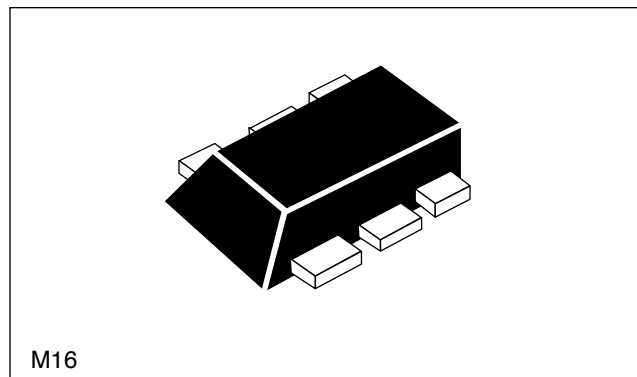


**NEC's NPN SiGe  
HIGH FREQUENCY TRANSISTOR**

**NESG2101M16**

**FEATURES**

- **HIGH BREAKDOWN VOLTAGE SiGe TECHNOLOGY**  
V<sub>CEO</sub> = 5 V (Absolute Maximum)
- **HIGH OUTPUT POWER:**  
P<sub>1dB</sub> = 21 dBm at 2 GHz
- **LOW NOISE FIGURE:**  
NF = 0.9 dB at 2 GHz  
NF = 0.6 dB at 1 GHz
- **HIGH MAXIMUM STABLE POWER GAIN:**  
MSG = 17 dB at 2 GHz
- **LOW PROFILE M16 PACKAGE:**  
6-pin lead-less minimold



**DESCRIPTION**

NEC's NESG2101M16 is fabricated using NEC's high voltage Silicon Germanium process (UHS2-HV), and is designed for a wide range of applications including low noise amplifiers, medium power amplifiers, and oscillators

**ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C)

PART NUMBER PACKAGE OUTLINE		NESG2101M16 M16				
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX	
RF	P <sub>1dB</sub>	Output Power at 1 dB Compression Point V <sub>CE</sub> = 3.6 V, I <sub>CQ</sub> = 10 mA, f = 2 GHz, Z <sub>S</sub> = Z <sub>SOPT</sub> , Z <sub>L</sub> = Z <sub>LOPT</sub>	dBm	21		
	GL	Linear Gain, V <sub>CE</sub> = 3.6 V, I <sub>CQ</sub> = 10 mA, f = 2 GHz,	dB	15		
	NF	Noise Figure at V <sub>CE</sub> = 2 V, I <sub>C</sub> = 10 mA, f = 2 GHz, Z <sub>S</sub> = Z <sub>SOPT</sub> , Z <sub>L</sub> = Z <sub>LOPT</sub>	dB		0.9	1.2
	G <sub>a</sub>	Associated Gain at V <sub>CE</sub> = 2 V, I <sub>C</sub> = 10 mA, f = 2 GHz, Z <sub>S</sub> = Z <sub>SOPT</sub> , Z <sub>L</sub> = Z <sub>LOPT</sub>	dB	11.0	13.0	
	NF	Noise Figure at V <sub>CE</sub> = 2 V, I <sub>C</sub> = 7mA, f = 1 GHz, Z <sub>S</sub> = Z <sub>SOPT</sub> , Z <sub>L</sub> = Z <sub>LOPT</sub>	dB		0.6	
	G <sub>a</sub>	Associated Gain at V <sub>CE</sub> = 2 V, I <sub>C</sub> = 7 mA, f = 1 GHz, Z <sub>S</sub> = Z <sub>SOPT</sub> , Z <sub>L</sub> = Z <sub>LOPT</sub>	dB		19.0	
	MSG	Maximum Stable Gain <sup>1</sup> at V <sub>CE</sub> = 3 V, I <sub>C</sub> = 50 mA, f = 2 GHz	dB	14.5	17.0	
	IS <sub>21E</sub> <sup>2</sup>	Insertion Power Gain at V <sub>CE</sub> = 3 V, I <sub>C</sub> = 50 mA, f = 2 GHz	dB	11.5	13.5	
	f <sub>T</sub>	Gain Bandwidth Product at V <sub>CE</sub> = 3 V, I <sub>C</sub> = 50 mA, f = 2 GHz	GHz	14	17	
	C <sub>re</sub>	Reverse Transfer Capacitance <sup>2</sup> at V <sub>CB</sub> = 2 V, I <sub>E</sub> = 0 mA, f = 1 MHz	pF		0.4	0.5
DC	I <sub>CBO</sub>	Collector Cutoff Current at V <sub>CB</sub> = 5V, I <sub>E</sub> = 0	nA			100
	I <sub>EBO</sub>	Emitter Cutoff Current at V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0	nA			100
	h <sub>FE</sub>	DC Current Gain <sup>3</sup> at V <sub>CE</sub> = 2 V, I <sub>C</sub> = 15 mA		130	190	260

Notes:

1.  $MSG = \left| \frac{S_{21}}{S_{12}} \right|$
2. Collector to base capacitance when the emitter pin is grounded.
3. Pulsed measurement, pulse width ≤ 350 μs, duty cycle ≤ 2 %.

**ABSOLUTE MAXIMUM RATINGS<sup>1</sup>** (T<sub>A</sub> = 25°C)

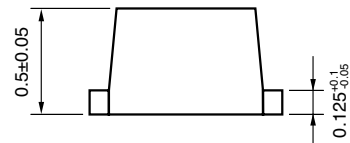
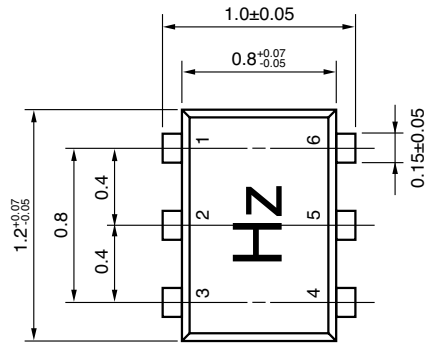
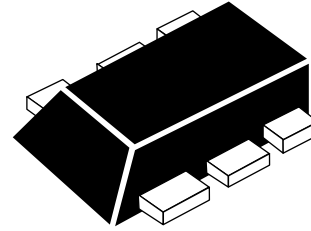
SYMBOLS	PARAMETERS	UNITS	RATINGS
V <sub>CB0</sub>	Collector to Base Voltage	V	13.0
V <sub>CEO</sub>	Collector to Emitter Voltage	V	5.0
V <sub>EBO</sub>	Emitter to Base Voltage	V	1.5
I <sub>C</sub>	Collector Current	mA	100
P <sub>T</sub> <sup>2</sup>	Total Power Dissipation	mW	190
T <sub>J</sub>	Junction Temperature	°C	150
T <sub>STG</sub>	Storage Temperature	°C	-65 to +150

Note:

1. Operation in excess of any one of these parameters may result in permanent damage.
2. Mounted on 1.08 cm<sup>2</sup> x 1.0 mm (t) glass epoxy PCB.

**OUTLINE DIMENSIONS** (Units in mm)

**PACKAGE OUTLINE M16  
6-PIN LEAD-LESS MINIMOLD**



**ORDERING INFORMATION**

PART NUMBER	QUANTITY	SUPPLYING FORM
NESG2101M16-T3-A	10 K pcs reel	Pin 1 (Collector), Pin 6 (Emitter) face the perforation side of the tape

**PIN CONNECTIONS**

- |              |            |
|--------------|------------|
| 1. Collector | 4. Base    |
| 2. Emitter   | 5. Emitter |
| 3. Emitter   | 6. Emitter |

**Life Support Applications**

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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DATA SUBJECT TO CHANGE WITHOUT NOTICE

11/13/2003

Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (\*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL’s understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
		-A	-AZ
Lead (Pb)	< 1000 PPM	Not Detected	(*)
Mercury	< 1000 PPM	Not Detected	
Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
PBB	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

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